

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 1, line 8, with the following amended paragraph:

Non-provisional United States Patent Application Serial No. 10/273,041, filed October 10, 2002, now U.S. Patent No. 6,632,694, entitled DOUBLE HETEROJUNCTION LIGHT EMITTING DIODES AND LASER DIODES HAVING QUANTUM DOT SILICON CARBIDE EMITTERS, assigned to Astralux, Inc., incorporated herein by reference, provides for the fabrication of silicon-based light emitting diodes using nano-patterning and direct-wafer-bonding.

Please replace the paragraph beginning at page 3, line 20, with the following amended paragraph:

HBT 10 includes (1) a first Si n-type emitter layer 11 and its contact layer 12, (2) a second Si n-type emitter layer 13 and its contact layer 14, (3) a p-type Si base layer 15 and its three contact layers 16, 17, and 18, (4) an n-type SiC collector layer 19, and (5) an n-type SiC sub-collector layer 20 having a contact layer 21, wherein sub-collector layer 20 may be more heavily doped than collector layer 19, thus improving the ohmic contact to the collector layer 19.